《风光欣》技术资料

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2SD1468

NPN Muting Transistor

Featres 15V 1A

Low saturatlon voltage,typicalty $V_{CE(sat)}$=0.006V at Ic/I_B=1mA/0.1mA

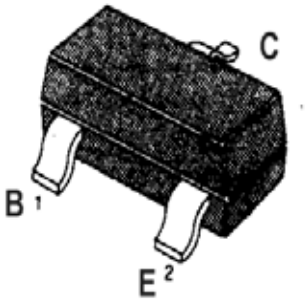
Ideal for low voltage high current drives

High DC current gain and high current

ABSOLUTE MAXIMUM RATINGS(Ta=25 ℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	Ic	1	A
Collector Dissipation	Pc	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~150	℃

SOT-23



ELECTRCAL CHARACTERISTICS(Ta=25 ℃)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-to-Base Breakdown Voltage	BV_{CBO}	Ic= 50 μ A,I_E= 0	30			V
Collector-Emitter Saturation Voltage	BV_{CEO}	Ic= 1mA,	15			V
Emitter-to-Base Breakdown Voltage	BV_{EBO}	I_E= 50 μ A,I_C= 0	5			V
Collector-Cutoff Current	I_{CB0}	V_{CB}= 20V,I_E=0			0.5	μ A
Emitter-Cutoff Current	I_{EB0}	V_{EB}= 4V,Ic=0			0.5	μ A
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$	Ic= 500mA,I_B= 50mA		0.08	0.4	V
*DC Current Gain	Hfe	V_{CE}= 3V,Ic= 0.1A	120		560	
Transition Frequency	f_T	V_{CE}= 5V,I_C=1A,f=100MHZ	50	150		MHZ
Output Capacitance	C_{OB}	V_{CB} = 10V,I_E=0,f=1MHZ		15	30	pF